# **Special Function Logic Gate**

# NLSF457

#### Description

The NLSF457 is a single special function gate in tiny footprint package.

#### **Features**

- Designed for 1.65 V to 5.5 V V<sub>CC</sub> Operation
- 2.7 ns t<sub>PD</sub> at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- I<sub>OFF</sub> Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Available in 1.45 mm x 1.0 mm UDFN8 Package
- Chip Complexity < 100 FETs
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

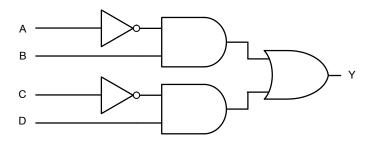


Figure 1. Logic Diagram



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UDFN8, 1.45x1, 0.35P CASE 517EB

#### **MARKING DIAGRAM**



XX = Specific Device CodeM = Assembly Operation Code\*

= Pb-Free Package

(Note: Microdot may be in either location)
\*Assembly Operation Code orientation and/or may
vary depending upon manufacturing location.

#### **PIN ASSIGNMENT**

nc	11.	8	Vcc
D	2	7	Υ
С	3	6	Α
GND	4	5	В

Pin	Name	Description
1	nc	No Connect
2	D	Input
3	С	Input
4	GND	Ground
5	В	Input
6	Α	Input
7	Υ	Output
8	V <sub>CC</sub>	Power Supply

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

**Table 1. FUNCTION TABLE** 

	Input				
Α	В	С	D	Υ	
0	0	0	0	0	
0	0	0	1	1	
0	0	1	0	0	
0	0	1	1	0	
0	1	0	0	1	
0	1	0	1	1	
0	1	1	0	1	
0	1	1	1	1	
1	0	0	0	0	
1	0	0	1	1	
1	0	1	0	0	
1	0	1	1	0	
1	1	0	0	0	
1	1	0	1	1	
1	1	1	0	0	
1	1	1	1	0	

#### **MAXIMUM RATINGS**

Symbol	Parame	eter	Ratings	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +6.5	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +6.5	V
V <sub>OUT</sub>	DC Output Voltage	Active-Mode (High or Low State)	-0.5 to V <sub>CC</sub> +0.5	V
		Tri-State Mode (Note 1)	-0.5 to +6.5	
		Power–Down Mode (V <sub>CC</sub> = 0 V)	-0.5 to +6.5	
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-50	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>OUT</sub> < GND	-50	mA
I <sub>OUT</sub>	DC Output Source/Sink Current		±50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC Supply Current Per Supply Pin or Ground Pin		±100	mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C	
TL	Lead Temperature, 1 mm from Case for 10	Seconds	260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	UDFN8	231	°C/W
$P_{D}$	Power Dissipation in Still Air at 125°C	UDFN8	541	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage (Note 3)	Charged Device Model	> 2000	V
		Human Body Model	> 1000	
I <sub>LATCHUP</sub>	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- Measured with minimum pad spacing on an FR4 board, using 10mm by 1inch, 2 ounce copper trace no air flow per JESD51–7.
   HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101–F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	Digital Input Voltage		0	5.5	V
V <sub>OUT</sub>	Output Voltage	ttput Voltage Active Mode (High or Low State)		V <sub>CC</sub>	V
		Tri-State Mode (Note 1)	0	5.5	
		Power Down Mode (V <sub>CC</sub> = 0 V)	0	5.5	
T <sub>A</sub>	Operating Free-Air Temperature		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Transition Rise or Fall Rate	V <sub>CC</sub> = 1.65 V to 1.95 V	0	20	nS/V
		V <sub>CC</sub> = 2.3 V to 2.7 V	0	20	
		V <sub>CC</sub> = 3.0 V to 3.6 V	0	10	
		V <sub>CC</sub> = 4.5 V to 5.5 V	0	5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

					T <sub>A</sub> = 25°C		T <sub>A</sub> = -55°C	c to +125°C	
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level		1.65 to 1.95	0.65 x V <sub>CC</sub>	-	-	0.65 x V <sub>CC</sub>	-	V
	Input Voltage		2.3 to 5.5	0.70 x V <sub>CC</sub>	-	-	0.70 x V <sub>CC</sub>	_	
V <sub>IL</sub>	Low-Level		1.65 to 1.95	-	-	0.35 x V <sub>CC</sub>	-	0.35 x V <sub>CC</sub>	V
	Input Voltage		2.3 to 5.5	_	-	0.30 x V <sub>CC</sub>	-	0.30 x V <sub>CC</sub>	
V <sub>OH</sub>	High-Level Output Voltage	$\begin{split} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -100  \mu A \\ I_{OH} &= -4  \text{ mA} \\ I_{OH} &= -8  \text{ mA} \\ I_{OH} &= -12  \text{ mA} \\ I_{OH} &= -16  \text{ mA} \\ I_{OH} &= -24  \text{ mA} \\ I_{OH} &= -32  \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V <sub>CC</sub> - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V <sub>CC</sub> 1.4 2.1 2.4 2.7 2.5 4.0	-	V <sub>CC</sub> - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	-	<b>V</b>
V <sub>OL</sub>	Low-Level Output Voltage	$\begin{aligned} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OL} &= 100  \mu\text{A} \\ I_{OL} &= 4 \text{ mA} \\ I_{OL} &= 8 \text{ mA} \\ I_{OL} &= 12 \text{ mA} \\ I_{OL} &= 16 \text{ mA} \\ I_{OL} &= 24 \text{ mA} \\ I_{OL} &= 32 \text{ mA} \end{aligned}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	-	0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55	-	0.1 0.24 0.3 0.4 0.4 0.55	٧
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	1.65 to 5.5	-	-	±0.1	-	±1.0	μΑ
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0	-	ı	1.0	-	10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	-	-	1.0	-	10	μА

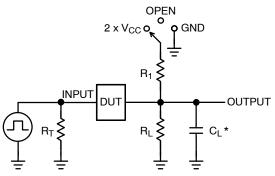
#### **AC ELECTRICAL CHARACTERISTICS**

				T <sub>A</sub> = 25°C		T <sub>A</sub> = -55°C to +125°C			
Symbol	Characteristic	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation Delay,	$R_L = 1 M\Omega$ , $C_L = 15 pF$	1.65 to 1.95	-	7.7	10	-	10.5	ns
t <sub>PHL</sub>	(A or B or C or D) to Y	$R_L = 1 \text{ M}\Omega$ , $C_L = 15 \text{ pF}$	2.3 to 2.7	-	4.2	7.5	-	8.0	
	(Figures 3 and 4)	$R_L = 1 \text{ M}\Omega$ , $C_L = 15 \text{ pF}$	3.0 to 3.6	-	3.0	5.2	-	5.5	
		$R_L = 500 \Omega, C_L = 50 pF$		-	3.5	5.7	-	6.0	
		$R_L = 1 \text{ M}\Omega$ , $C_L = 15 \text{ pF}$	4.5 to 5.5	-	2.3	4.5	-	4.8	
		$R_L = 500 \Omega$ , $C_L = 50 pF$		1	2.6	5.0	-	5.3	

## **CAPACITAVE CHARACTERISTICS**

Symbol	Parameter	Test Condition	Typical (T <sub>A</sub> = 25 °C)	Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 5.5 V, $V_{IN}$ = 0 V or $V_{CC}$	2.5	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC}$ = 5.5 V, $V_{IN}$ = 0 V or $V_{CC}$	2.5	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 5)	10 MHz, V <sub>CC</sub> = 3.3 V, V <sub>IN</sub> = 0 V or V <sub>CC</sub>	9	pF
		10 MHz, V <sub>CC</sub> = 5.5 V, V <sub>IN</sub> = 0 V or V <sub>CC</sub>	11	

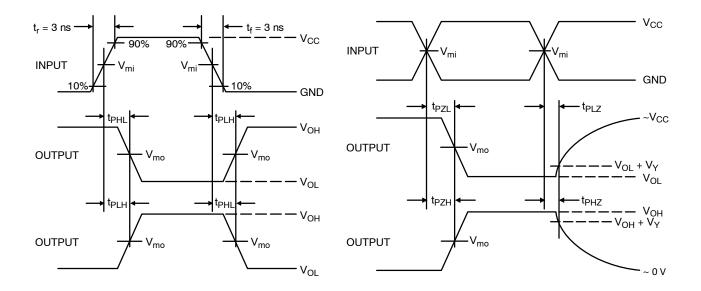
<sup>5.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.



Test	Switch Position	C <sub>L</sub> , pF	$R_L, \Omega$	$R_{1}, \Omega$	
t <sub>PLH</sub> / t <sub>PHL</sub>	Open	See AC Characteristics Table			
t <sub>PLZ</sub> / t <sub>PZL</sub>	2 x V <sub>CC</sub>	50	500	500	
t <sub>PHZ</sub> / t <sub>PZH</sub>	GND	50	500	500	

 $C_L$  includes probe and jig capacitance  $R_T$  is  $Z_{OUT}$  of pulse generator (typicaly 50  $\Omega)$  f = 1 MHz

Figure 2. Test Circuit



		V <sub>m</sub>		
V <sub>CC</sub> , V	V <sub>mi</sub> , V	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub> , t <sub>PZH</sub> , t <sub>PHZ</sub>	V <sub>Y</sub> , V
1.65 to 1.95	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.15
2.3 to 2.7	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.15
3.0 to 3.6	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.3
4.5 to 5.5	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.3

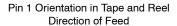
Figure 3. Switching Waveforms

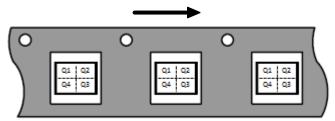
#### **ORDERING INFORMATION**

Device	Package	Marking	Pin 1 Orientation (see bellow)	Shipping <sup>†</sup>
NLSF457MU3TCG	UDFN8, 1.45 x 1.0, 0.35P	AA	Q4	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup> NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC – Q100 Qualified and PPAP Capable.





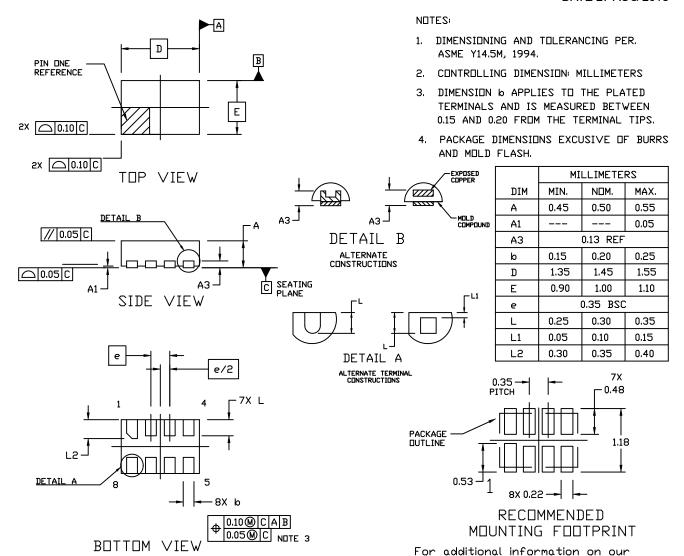
Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.





#### UDFN8, 1.45x1.0, 0.35P CASE 517EB ISSUE O

**DATE 27 AUG 2018** 



# GENERIC MARKING DIAGRAM\*



XX = Specific Device Code M = Date Code \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON97212G	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	UDFN8, 1.45x1.0, 0.35P		PAGE 1 OF 1		

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